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APPLICATION NO.	FILING DA	ATE	FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.		
10/672,884	09/26/20	03	Jae-Jong Han	2522-040 9537			
20575	7590 00	6/22/2004		EXAMINER			
	JOHNSON & N	LEE, HSIE	LEE, HSIEN MING				
	ORRISON STRE D, OR 97205	ET		ART UNIT	ART UNIT PAPER NUMBER		
101112111	, 011 7720			2823			
				DATE MAILED: 06/22/2004			

Please find below and/or attached an Office communication concerning this application or proceeding.

	Application No.	Applicant(s)					
Office Action Summers	10/672,884	HAN ET AL.	<u>i</u> k				
Office Action Summary	Examin r	Art Unit					
	Hsien-Ming Lee	2823					
Th MAILING DATE of this communication app Period for Reply	ars on the cov r sheet with the c	orrespondence ad	ldress				
A SHORTENED STATUTORY PERIOD FOR REPLY THE MAILING DATE OF THIS COMMUNICATION. - Extensions of time may be available under the provisions of 37 CFR 1.13 after SIX (6) MONTHS from the mailing date of this communication. - If the period for reply specified above is less than thirty (30) days, a reply - If NO period for reply is specified above, the maximum statutory period w - Failure to reply within the set or extended period for reply will, by statute, Any reply received by the Office later than three months after the mailing earned patent term adjustment. See 37 CFR 1.704(b).	36(a). In no event, however, may a reply be time within the statutory minimum of thirty (30) days will apply and will expire SIX (6) MONTHS from cause the application to become ABANDONEI	nely filed s will be considered timel the mailing date of this c O (35 U.S.C. § 133).					
Status		•					
1) Responsive to communication(s) filed on	_•						
2a) ☐ This action is FINAL . 2b) ☒ This	action is non-final.						
3) Since this application is in condition for allowar closed in accordance with the practice under E	· · · · · · · · · · · · · · · · · · ·		e merits is				
Disposition of Claims							
 5) Claim(s) 10-20 is/are allowed. 6) Claim(s) 1,2,4 and 9 is/are rejected. 7) Claim(s) 3 and 5-8 is/are objected to. 	Claim(s) <u>1-20</u> is/are pending in the application. 4a) Of the above claim(s) is/are withdrawn from consideration. Claim(s) <u>10-20</u> is/are allowed. Claim(s) <u>1,2,4 and 9</u> is/are rejected.						
Application Papers							
9)☐ The specification is objected to by the Examine 10)☒ The drawing(s) filed on is/are: a)☒ access Applicant may not request that any objection to the confidence Replacement drawing sheet(s) including the correction of the oath or declaration is objected to by the Examine 11)☐ The oath or declaration is objected to by the Examine 10.	epted or b) objected to by the Eddrawing(s) be held in abeyance. See ion is required if the drawing(s) is obj	e 37 CFR 1.85(a). ected to. See 37 C					
Priority under 35 U.S.C. § 119							
12) Acknowledgment is made of a claim for foreign a) All b) Some * c) None of: 1. Certified copies of the priority documents 2. Certified copies of the priority documents 3. Copies of the certified copies of the prior application from the International Bureau * See the attached detailed Office action for a list	s have been received. s have been received in Applicati ity documents have been receive u (PCT Rule 17.2(a)).	on No ed in this National	Stage				
	Min /	Min I					
Attachment(s) 1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449 or PTO/SB/08) Paper No(s)/Mail Date	4) Interview Summary Paper No(s)/Mail Da 5) Notice of Informal P 6) Other:	ate	•				

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DETAILED ACTION

Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the

basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(b) the invention was patented or described in a printed publication in this or a foreign country or in public use or on

sale in this country, more than one year prior to the date of application for patent in the United States.

2. Claims 1, 2, 4 and 9 are rejected under 35 U.S.C. 102(b) as being anticipated by Tomio et

al. (JP11-345970, submitted by applicant).

In re claims 1-2, 4 and 9, Tomio et al. in Figs. 1-4 and related text teach the claimed

method of forming a gate electrode comprising:

* forming a gate structure on a semiconductor substrate 12, the gate structure having a gate

oxide film pattern 26, a N-doped polysilicon film pattern 28, and a tungsten silicide film

pattern 30; and

forming a first oxide film 42 on a sidewall of the gate structure 26/28/30 and on the

semiconductor substrate 12 by re-oxidizing (i.e. a thermal oxidation at a first RTP) the gate

structure 26/28/03 and the substrate under an atmosphere including an oxygen gas (i.e. 20% or

less of O2) and an inert gas (i.e. N2), wherein a portion of the first oxide film 42 is formed on a

sidewall of the polysilicon film pattern 28 has a thickness substantially identical to that of a

portion of the first oxide film 42 formed on a sidewall of the metal silicide film pattern 30

(paragraphs [0012], [0031].

Allowable Subject Matter

3. Claims 10-20 are allowed.

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4. Claims 3, 5-8 are objected to as being dependent upon a rejected base claim, but would be allowable if rewritten in independent form including all of the limitations of the base claim and any intervening claims.

5. The following is a statement of reasons for the indication of allowable subject matter:

The prior art of record neither teaches nor suggest that the oxygen gas and the inert gas ranges between about 1.0:0.9 and about 1.0:1.1 (claim 3); setting a temperature at about 400~480 °C and raising the temperature to 800~900 °C while the inert gas is provided into the furnace (claim 5); forming a second oxide film on the first oxide film by oxidizing using an oxygen gas and a mixture of oxygen and chlorine-containing gas (claim7); forming nitride spacers and self-aligned contact (claim 10); raising a temperature having a second temperature higher than the first temperature while a first inert gas us introduced into the furnace and re-oxidizing by using an oxygen gas and a second inert gas (claim 15).

6. Any inquiry concerning this communication or earlier communications from the examiner should be directed to Hsien-Ming Lee whose telephone number is 571-272-1863. The examiner can normally be reached on M-F (9:00 \sim 5:00).

If attempts to reach the examiner by telephone are unsuccessful, the examiner's supervisor, Olik Chaudhuri can be reached on 571-272-1855. The fax phone number for the organization where this application or proceeding is assigned is 703-872-9306.

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Information regarding the status of an application may be obtained from the Patent Application Information Retrieval (PAIR) system. Status information for published applications may be obtained from either Private PAIR or Public PAIR. Status information for unpublished applications is available through Private PAIR only. For more information about the PAIR system, see http://pair-direct.uspto.gov. Should you have questions on access to the Private PAIR system, contact the Electronic Business Center (EBC) at 866-217-9197 (toll-free).

Hsien-Ming Lee

June 21, 2004

Primary Examiner Art Unit 2823

Bries My Lu 6/164

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